Cubic β -WN_x layers: growth and properties vs N-to-W ratio

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Tungsten nitride layers, 1.45- μ m-thick, were deposited by reactive magnetron sputtering on MgO(001), MgO(111), and Al₂O₃(0001) in 20 mTorr N₂ at $T_s = 500$ -800 °C. All layers deposited at $T_s = 500$ -700 °C form a cubic phase, as determined by X-ray diffraction ω -2 θ scans, and show an N-to-W ratio x that decreases from $x = 1.21$ to 0.83 with increasing $T_s = 500$ -700 °C, as measured by energy dispersive and photoelectron spectroscopies. $T_s = 500$ and 600 °C yields polycrystalline predominantly 111 oriented β -WN on all substrates. In contrast, deposition at 700 °C results in epitaxial growth of β -WN(111) and β -WN(001) on MgO(111) and MgO(001), respectively, and a 111-preferred orientation on Al₂O₃(0001). $T_s = 800$ °C causes nitrogen loss and WN_x layers with primarily BCC W grains and $x = 0.04$ -0.06. Density functional theory calculations indicate an increase in structural stability by the introduction of either W or N vacancies into the cubic rock-salt structure, reducing the formation energy per atom from 0.32 eV for the rock-salt structure to 0.09 eV for WN_{0.75} and -0.07 eV for WN_{1.33}, to -0.42 eV for stoichiometric WN in the NbO structure. The out-of-plane lattice constant decreases from 4.357-4.169 Å with increasing $T_s = 500$ -700 °C. Comparing these values with calculated lattice constants indicates that the W vacancy concentration increases from 6-11% for $T_s = 500$ -600 °C to 11-18% for $T_s = 700$ °C, while the N vacancy concentration also increases from negligible to 18-29%. The simultaneous increase of both vacancy types is attributed to thermally activated N₂ recombination and desorption and atomic rearrangement towards the thermodynamically favorable cubic NbO structure which contains 25% of both W and N vacancies. The measured elastic modulus ranges from 110-260 GPa for 500-700 °C and decreases with increasing N-content, and increases to 350 GPa for $T_s = 800$ °C. The room temperature resistivity decreases with increasing $T_s = 500$ -700 °C from 4.5 - 1.1×10^3 $\mu\Omega$ -cm, indicating a resistivity decrease with decreasing nitrogen content and increasing crystalline quality and phase purity.

Keywords: Tungsten nitride; cubic; nitrogen vacancy; hardness; density functional calculations; lattice constant

1. Introduction

Transition metal nitrides are known for their high hardness, wear and corrosion resistance, and high temperature stability [1–3], and are therefore widely used as hard wear-protective coatings, diffusion barriers in microelectronics, and optical or decorative coatings [4,5]. Many computational and experimental studies focus on the analysis of stoichiometric samples [6–10]. However, the properties of transition metal nitrides can vary widely as a function of the anion to cation ratio x . For example, the hardness of TiN_x decreases from 30 ± 2 to 20.2 ± 2 GPa and its electrical resistivity decreases from 192 to $13 \mu\Omega\text{-cm}$ as x increases from 0.67 to 1.00 while retaining the single cubic phase [11,12]. In addition, many transition metal nitrides including HfN_x [13], TiN_x [11], CeN_x [14], ZrN_x , [15], TaN_x [16] and NbN_x [17] crystallize in a range of different phases, resulting in additional variations in physical properties. That is, the nitrogen-to-metal ratio affects both the crystal structure, i.e. the phase, and the composition of this phase as manifested by point defects including metal and/or nitrogen vacancies and anti-site substitutions [18]. The understanding of how the crystal structure and the point defect concentration of transition metal nitride layers changes with composition and deposition conditions is important in order to develop protective coatings with desired properties, since these properties are affected by both the crystal structure and the defect concentration.

Tungsten nitride exhibits a variety of phases over a large composition range $x = 0.5\text{--}2.0$ [19–22]. The most commonly reported WN_x phases are stoichiometric hexagonal $\delta\text{-WN}$ and cubic $\beta\text{-W}_2\text{N}$, which is a rocksalt-type structure where 50% of the N-sites are vacant [19,20]. In addition, there are reports on hexagonal and rhombohedral W_2N_3 and cubic W_3N_4 phases which have been synthesized using high pressure and high temperature [22]. Reports from first-principles computational studies propose a high-bulk-modulus WN_2 phase [21], a cubic NbO

structure for stoichiometric WN [23–25], a tungsten-deficient rhombohedral $r\text{-W}_2\text{N}_3$ [25], as well as metastable phases including, for example, a hexagonal $\delta\text{-W}_2\text{N}_3$ structure [25]. Interestingly, these studies found no stable cubic $\beta\text{-W}_2\text{N}$ structure and the cubic rock-salt-based $\beta\text{-WN}$ structures are only stable when containing W vacancies [25]. Nevertheless, experimental studies typically interpret that cubic $\beta\text{-WN}_x$ exhibits a rock-salt structure [JCPDF 00-025-1257], as x-ray diffraction data matches fcc-structure reflections with, however, a lattice parameter that varies from 4.11-4.30 Å [26–30] and a reported outlier of 3.9 Å possibly due to a low nitrogen concentration [30]. The predicted stable phase for stoichiometric ($x = 1$) WN_x is the cubic NbO structure [23,25], which can be described as a rock-salt structure containing a regular array of 25% cation and 25% anion vacancies [31]. We envision that deviations from stoichiometric compositions may be the result of these vacancies being filled. More specifically, cubic $\beta\text{-WN}_x$ structures with understoichiometric compositions $0.75 \leq x < 1$ may form by anion vacancies of NbO-structure WN being filled by W atoms, and correspondingly, $\beta\text{-WN}_x$ with $x = 1\text{--}1.33$ is obtained by filling cation vacancies with N atoms.

The composition of tungsten nitride layers is affected by deposition parameters and method, which include reactive DC magnetron sputtering [26–28,30,32–37], reactive pulsed laser deposition [34,38,39], RF sputtering [40–42], cathodic arc deposition [43], atomic layer deposition [44], and chemical vapor deposition [29,45–47]. DC reactive magnetron sputtering in a Ar+N_2 mixture has been reported to yield $x = 0.33$ with a N_2 fraction in the gas of $f_{\text{N}_2} = 10\%$ [30], or $x = 0\text{--}0.5$ with f_{N_2} increasing from 0-75% [36], but also $x = 0\text{--}1.1$ for $f_{\text{N}_2} = 0\text{--}75\%$ [32], $x = 0\text{--}1.2$ for $f_{\text{N}_2} = 0\text{--}63\%$ [28], and $x = \sim 0\text{--}1.2$ for $f_{\text{N}_2} = 5\%$ with an increasing 17-26 Pa total pressure [37]. However, the layers with high N content $x > 0.9$ have a tendency to exhibit a hexagonal WN phase [28,40]. RF sputter deposition yields in many cases even higher nitrogen

concentrations (again exhibiting a hexagonal phase for high x), likely due to energetic implantation, with $x = 0.6$ - 1.6 for $f_{\text{N}_2} = 10$ - 75% [41], $x = 1.1$ - 1.4 for $f_{\text{N}_2} = 10$ - 60% [42], $x = 0.11$ - 0.25 for $P_{\text{N}_2} = 0$ - 1.6 Pa with a constant 0.53 Pa Ar [34], and $x = 0.35$ - 1.17 for $f_{\text{N}_2} = 38$ - 83% [40]. Pulsed laser deposition (PLD) can also lead to a wide range of nitrogen contents including $x = 0.17$ - 0.5 in 1.33 - 8 Pa N_2 [34] and a high nitrogen content of $x = 1.76$ in 75 mTorr N_2 [39]. In comparison to these previously reported concentration ranges for cubic β - WN_x , our layers have a relatively high nitrogen concentration.

In this study, we report on polycrystalline and epitaxial WN_x layers deposited on single crystal $\text{MgO}(001)$, $\text{MgO}(111)$, and $\text{Al}_2\text{O}_3(0001)$ substrates. The layers deposited from $T_s = 500$ - 700 °C have relatively large N/W ratios ranging from $x = 0.83 - 1.21$ and exhibit a pure cubic β -phase, indicating that the composition range for β - WN_x can be extended from well below to well above the stoichiometric $x = 1$, which is opposite to the reported formation of a hexagonal phase for WN_x with $x > 0.9$ [28,40]. The nitrogen content x decreases with increasing growth temperature and nearly vanishes for $T_s = 800$ °C, yielding WN_x layers with a predominantly BCC W structure. Density functional theory (DFT) calculations provide a confirmation of lattice constant trends observed with decreasing nitrogen content. In addition, DFT computations are also used to examine the relative stabilities of rock-salt and NbO structures of WN_x as a function of x . They indicate a negative formation energy for the formation of both W and N vacancies and provide a framework to explain the increasing vacancy concentrations on both cation and anion sublattices with increasing T_s . Nanoindentation results show similar hardness trends for all three substrates ranging from 9.7 - 12.9 GPa for WN_x deposited from 500 - 700 °C, within the reported hardness H values for WN_x of 5 - 39 GPa [28,33,34,38,40,43], while the elastic moduli vary considerably with N-content and texture, ranging from 110 - 260 GPa, which is lower than

previously reported values of $E = 240\text{-}430$ GPa [32,34,40]. In addition, four point probe measurements show a decrease in resistivity with increasing substrate temperature due to a combination of increasing crystal quality and decreasing nitrogen content.

2. Experimental Procedure

WN_x layers were deposited on MgO(001), MgO(111) and Al₂O₃(0001) substrates in a load-locked ultra-high vacuum (UHV) dc magnetron sputtering system with a base pressure of $<10^{-9}$ torr [17,48]. The substrates are one-side polished $10\times10\times0.5$ mm³ wafers that were cleaned in successive rinses of trichloroethylene, acetone, isopropanol, and deionized water, blown dry with dry N₂, attached to a Mo block with silver paint, loaded into the system through a load-lock chamber, and thermally degassed at 900 °C for 1 hour. The substrate temperature T_s was measured by a thermocouple below the sample stage that was cross-calibrated with a pyrometer focusing on the sample surface. T_s was lowered to 500-800 °C prior to deposition from a 99.95%-pure 51-mm-diameter W target which was sputter etched for 5 minutes with a shutter shielding the substrate. The target was facing the substrate at a 9 cm distance and from a 45° angle, with the substrate being continuously rotated at 60 min⁻¹ to increase thickness uniformity. A constant dc power of 300 W was applied to the magnetron, yielding a deposition rate of 375 nm/hr in 20 mTorr 99.999% pure N₂.

X-ray diffraction was done in a Panalytical X'Pert PRO MPD system with a Cu K_α $\lambda = 1.5418$ Å source yielding a 1° divergent incident beam limited by an incident slit. ω - 2θ scans were collected over a 2θ range from 5° - 90° using the Bragg-Brentano geometry and a PixCEL solid-state line detector. The 2θ -values were calibrated using the substrate peaks, that is, 2θ was set to the literature values of 36.947°, 42.909°, and 41.685° at the measured positions of the

MgO 111, MgO 002, and Al₂O₃ 0006 reflections measured using Cu K α ₁ x-rays, respectively. Energy-dispersive X-ray spectroscopy (EDS) spectra were collected in a FEI Helios Nanolab scanning electron microscope (SEM) with an accelerating voltage of 5.0 kV and a working distance of 5.0 mm. The EDS spectra were analyzed with the Oxford Instruments AZtec EDS software to determine the N-to-W composition ratio of each sample. The composition values are expected to be accurate to within $\pm 3\%$, based on test measurements on BN and CaSiO₃ standards that use the same Oxford Instruments X-Max^N 80 silicon drift detector used for the WN_x specimens and is particularly well suited for light element analysis. In addition, photoelectron spectroscopy (XPS) spectra were acquired for samples deposited at $T_s = 700$ °C using Al K α radiation (1486.7 eV) in a PHI Versaprobe system with a hemispherical analyzer and an 8-channel detector. All high resolution spectra were collected using a pass energy of 23.5 eV and a step size of 0.2 eV. The XPS analyses were done on as-deposited air exposed surfaces without sputter cleaning in order to not affect the measured N-to-W ratios by preferential sputtering effects.

The hardness and elastic modulus were measured using a Hysitron TI 900 Tribodenter nanoindenter which was calibrated using a fused quartz standard of known hardness and elastic modulus. A minimum of 10 indents were performed for each sample, using a diamond Berkovich tip with a nominal tip radius of 150 nm that was indented to a maximum load of 6 mN. H and E values of the layers were determined from the loading and unloading curves, using the Oliver and Pharr method [49] and an elastic modulus of 1140 GPa and a Poisson's ratio of 0.07 for the diamond indenter tip [50]. Resistivity measurements were done at room temperature (293 K) using a linear four point probe with 1-mm inter-probe spacings, a Keithley 2182A Nanovoltmeter, and a Keithley 6220 Precision Current Source providing ± 3 mA. The resistivity

was determined from the measured sheet resistance by correcting for the substrate geometry according to Ref. [51], and using the layer thickness of $1.45\ \mu\text{m}$ as measured by cross sectional SEM on cleaved samples.

3. Computational Method and Results

First-principles DFT calculations are performed using the Vienna *ab initio* simulation package (VASP), employing periodic boundary conditions, a plane wave basis set, the Perdew-Burke-Ernzerhof generalized gradient approximation exchange correlation functional [52], and the projector-augmented wave method [53]. All computational parameters are chosen such that calculated total energy differences are converged to within 5 meV/atom. This includes a 500 eV cut-off energy for the plane-wave basis set expansion and a Γ -centered $6\times 6\times 6$ k -point grid for WN_x super cells containing 48-64 atoms. W $4s$, $4p$, and $4d$ electrons are explicitly calculated, that is, they are not included in the core of the pseudo potential. Atomic positions and lattice parameters are relaxed iteratively while the cubic unit cell shape was kept fixed for all calculations. The simulated cubic supercells consist of 8 conventional unit cells which each contain 4 W and 4 N atomic sites, yielding a total of 64 atoms in the super cell for the rock-salt (NaCl) structure. The conventional unit cell of WN in the NbO structure belongs to the space group 221 (Pm-3m) with Wyckoff positions W 3c ($0, \frac{1}{2}, \frac{1}{2}$) and N 3d ($0, \frac{1}{2}, 0$), yielding a regular sublattice of 8 W and 8 N vacancies for the NbO structure supercell containing a total of 48 atoms. Off-stoichiometric cubic WN_x is simulated by varying the occupation on this sublattice. That is, starting with the NaCl structure, an increasing number of W or N sublattice sites are vacated, causing an increase or decrease in x , respectively. Correspondingly, starting from the NbO structure, W or N sublattice sites are filled with the respective atoms, causing a decrease or

increase in x , respectively. For each fixed number of W and N atoms, all possible occupation configurations on the sublattice have been calculated, and the results from the lowest energy configuration are reported in this paper. We note here that other vacancy configurations, i.e. with vacancies occupying other sites than those defined by the regular sublattice of the NbO structure, are not investigated in this study. Also, the generalized gradient approximation used in the calculations is known to typically overestimate lattice constants by approximately 1% [54], which is not corrected for in the below analysis, since there is no systematic method to correct for such lattice-constant errors except by using an alternative exchange correlation functional such as the PBEsol.

The cohesive energy E_c for the different structures is determined relative to BCC W and molecular nitrogen. That is, $E_c = E - N_W\mu_W - \frac{1}{2} N_N\mu_{N_2}$, where E is the calculated energy for a specific supercell containing N_W tungsten and N_N nitrogen atoms, while μ_W and μ_{N_2} are the W and N_2 chemical potentials corresponding to the calculated energy of one-atom BCC W unit cell and an isolated N_2 molecule, respectively. All calculations are for zero temperature. Considering finite temperatures would add correction terms, with the largest being associated with the entropy of the N_2 gas, driving the system at high temperature towards phase separation into N_2 gas and a reduction in x in the solid WN_x phase. In order to directly compare formation energies E_f of different configurations, the calculated cohesive energies are presented in this paper as energy per atom, i.e. $E_f = E_c/(N_W+N_N)$.

Figure 1 summarizes the computational results, showing the calculated formation energy and lattice constant of cubic WN_x vs N-to-W ratio $x = 0.75-1.33$. The starting point for all explored atomic configurations are the NaCl and NbO crystal structures, which have calculated formation energies of $E_f = 0.32$ and -0.42 eV, as shown in Fig. 1(a) at $x = 1.0$. The positive E_f

value for the rock-salt structure indicates that it is unstable against phase separation into BCC W and N₂ gas. In contrast, the NbO structure is stable, consistent with previous computational reports [23,25]. Off-stoichiometric configurations are simulated by creating or filling vacancies in the NaCl or NbO structures, respectively. The formation energy of WN_x in the rock-salt structure drops when introducing W vacancies [plotted as red circles in Fig. 1(a)], initially steeply from 0.32 to 0.04 eV for $x = 1.00$ -1.14 and then gently to -0.07 eV for $x = 1.33$. Similarly, N-vacancies also reduce E_f , reaching 0.11 eV for $x = 0.88$ and 0.09 eV for $x = 0.75$. Filling vacancies of the NbO structure results in an increase in the formation energy, as shown with the blue squares in Fig. 1(a). The increase is initially small, particularly for $x > 1$, but then reaches the same endpoints as the red data points for $x = 0.75$ and 1.33, which correspond to structures with conventional unit cells containing one N and one W vacancy, respectively. In addition, Fig. 1(a) also shows as triangular data point the formation energy for a stoichiometric WN structure with a 50% filling of both cation and anion vacancies in the NbO structure. The $E_f = -0.23$ eV of this structure is considerably closer to the NbO structure than the rock-salt formation energy, confirming the observed trend that the introduction of a small density of vacancies in the NaCl structure reduces E_f considerably more than the increase in E_f when filling some vacancy sites in the NbO structure.

Figure 1(b) is a corresponding plot of the calculated lattice constants. It is $a_{rs} = 4.357$ Å for the NaCl structure, and 5.3% smaller, $a_{NbO} = 4.124$ Å, for the NbO structure. As expected, introducing vacancies in rock-salt WN reduces a while filling vacant sites in the NbO structure increases a . This results in approximately linear changes in a as a function of x , as illustrated by the nearly straight dashed lines through the data points in Fig. 1(b). They are obtained using a

polynomial expression for the lattice constant as a function of the W and N vacancy concentrations V_W and V_N :

$$a = a_{rs} - \alpha V_W - \beta V_N - \gamma V_W V_N, \quad (1)$$

where the parameters $\alpha = 0.549 \text{ \AA}$, $\beta = 0.291 \text{ \AA}$ and $\gamma = 0.357 \text{ \AA}$ are determined to match the calculated lattice constants for $x = 0.75$, 1.0 , and 1.33 . Here V_W and V_N are in units of “sites” i.e. they correspond to the probability for a cation or anion site in the rock-salt structure to be vacant. A first test to check the validity of this expression is to calculate the lattice constant for the WN structure with 50% filling, i.e. $V_W = V_N = 0.125$, yielding a lattice constant of $4.246 \text{ \AA}$, which is just 0.16% larger than the directly calculated value for this structure of $4.239 \text{ \AA}$. This confirms the validity of the expression but also suggests that this structure with perfectly ordered vacancies may be slightly denser than predicted from a more random distribution of vacancies on the sublattice. The expression in Eq. (1) and the associated parameters α , β , and γ will in the following section be used to interpret the experimentally measured lattice constants.

4. Experimental Results and Discussion

Figure 2 shows representative sections of XRD θ - 2θ patterns, from WN_x layers deposited on $Al_2O_3(0001)$ at $T_s = 500, 600, 700$, and $800 \text{ }^\circ\text{C}$. For clarity purposes, the plotted intensities have been reduced by a factor of 50 for $41^\circ < 2\theta < 42.5^\circ$ near the intense substrate reflection for all patterns, and by a factor of 100 for the $T_s = 800 \text{ }^\circ\text{C}$ pattern for $38^\circ < 2\theta < 41^\circ$ near the intense BCC W 110 reflection. All layers exhibit a double peak feature at $2\theta = 41.685^\circ$ and 41.793° due to reflections of the Cu $K_{\alpha 1}$ and $K_{\alpha 2}$ lines at the substrate Al_2O_3 0006. The pattern from the layer deposited at $T_s = 500 \text{ }^\circ\text{C}$ exhibits a peak with 19 ± 1 cps at $2\theta = 35.96 \pm 0.20^\circ$, which is attributed to the 111 reflection for cubic β -WN. The angle is smaller than the reported value of $2\theta = 37.69^\circ$

(JCPDF 01-075-1012), indicating a larger lattice constant for our layers which is attributed to the high N-content as discussed below. In addition, this **pattern** shows a 7.6 times weaker peak at $2\theta = 64.0 \pm 0.3^\circ$ which is attributed to β -WN 220. No β -WN 002 peak is seen near the expected $2\theta = 43.8^\circ$, indicating a negligible concentration of 001 oriented grains which may be due to epitaxial effects during grain nucleation on $\text{Al}_2\text{O}_3(0001)$.

The layer has a strong 111-preferred orientation, since a random grain orientation is expected to lead to a β -WN 220 peak which is just 2.8 times smaller than the β -WN 111 peak [JCPDF 01-075-1012]. The **pattern** from the $T_s = 600^\circ\text{C}$ layer indicates a similar 111 preferred orientation, with the β -WN 111 peak at $2\theta = 36.06 \pm 0.13^\circ$ being 9.0 times stronger than the 220 peak. The 111 peak intensity is 36 ± 1 cps, which is 1.9 times larger than for $T_s = 500^\circ\text{C}$, indicating that the higher substrate temperature facilitates better long-range ordering, leading to a higher crystalline quality. However, the full-width at half-maximum remains relatively large, 1.7° and 1.5° for $T_s = 500$ and 600°C , indicating considerable strain variations and/or point defects which limit the x-ray coherence length along the growth direction in these samples. For comparison, these widths are ~ 5 times larger than the corresponding width from an epitaxial β -WN(111)/MgO(111) layer, which is included in the summary analyses below and has already been discussed in detail in Ref. [35]. Increasing T_s to 700°C results in a WN/ $\text{Al}_2\text{O}_3(0001)$ layer with an XRD **pattern**, shown in Fig. 2(a), which is still dominated by a relatively broad β -WN 111 peak with an intensity of 70 ± 2 cps. However, in contrast to $T_s \leq 600^\circ\text{C}$, the peak is shifted by 1.3° to the right, indicating a decreasing lattice constant which is attributed to an increasing N-vacancy concentration, as discussed below. **The peak is asymmetric, with a shoulder to the left of the peak maximum, indicating that some regions in this layer have a larger and varying lattice parameter (4.21 - $4.32 \text{ \AA}$) than the bulk of the sample with $4.17 \text{ \AA}$, consistent with Ref. [35].** In

addition, the **pattern** shows weaker peaks with 2 ± 1 , 6 ± 1 , and 2 ± 1 cps due to β -WN 002, 220, and 311 reflections, respectively, as well as small W 110 and 211 peaks with 12 ± 1 and 2 ± 1 cps at $2\theta = 40.24^\circ$ and $72.9\pm 0.2^\circ$, respectively. The presence of these latter two peaks indicates that this sample contains some grains with a BCC α -W phase, suggesting a reduction of the nitrogen content in this layer which is consistent with the compositional analyses presented below. This effect becomes much more pronounced at our highest deposition temperature of 800°C . The **pattern** shows a dominant W 110 peak with 7150 ± 50 cps, while the W 211 peak at $2\theta = 73.1\pm 0.1^\circ$ with 5 ± 1 cps is weak, suggesting a strong W 110 preferred orientation for this layer. In contrast to the lower deposition temperatures, the **pattern** shows no β -WN 111 peak but a β -WN 002 peak with 22 ± 1 cps. The peak at $2\theta = 43.74^\circ$ with 6 ± 1 cps is attributed to β -W (A-15 structure) [55] while the peak at $2\theta = 36.23^\circ$ is a measurement artifact, due to the K_β x-ray line. The dominance of the W reflections in this **pattern** suggests a reduced nitrogen concentration for layers deposited at $T_s = 800^\circ\text{C}$, consistent with a previous study suggesting nitrogen loss from tungsten nitrides at elevated temperatures ($>820^\circ\text{C}$) [56]. The slightly lower value for the temperature for nitrogen loss in our study may be related to different temperature calibration in the two studies. The peak position of the W 110 reflection indicates a lattice constant of $3.167\text{\AA}$ for the BCC W phase. This is 0.06% larger than the reported pure W lattice constant of $3.165\text{\AA}$, which indicates a slight lattice expansion that may be associated with interstitial nitrogen within the W lattice.

Similar x-ray diffraction analyses as those shown in Fig. 2(a) have also been done for layers grown on MgO(001) and MgO(111) substrates at $T_s = 500\text{--}800^\circ\text{C}$ (not shown). The results for growth on MgO(111) are similar to those presented above for $\text{Al}_2\text{O}_3(0001)$ substrates. In particular, the **patterns** for $T_s = 500, 600$, and 700°C are dominated by β -WN 111 peaks at $2\theta = 35.6\pm 1.0^\circ$, $36.2\pm 1.0^\circ$, and $37.359\pm 0.001^\circ$, respectively, while $T_s = 800^\circ\text{C}$ leads to an intense

W 110 peak of $8.20 \pm 0.05 \times 10^3$ cps but no detectable WN peak. Growth on MgO(001) results in dominant β -WN 111 peaks for $T_s = 500$ -600 °C, but a strong β -WN 002 peak at $2\theta = 42.7 \pm 0.1^\circ$ with $2.0 \pm 0.2 \times 10^3$ cps for $T_s = 700$ °C which is attributed to epitaxial growth as we have already previously reported in Ref. [35], while $T_s = 800$ °C again yields BCC W.

Figure 2(b) summarizes the XRD results from all samples in this study including those presented in detail in Fig. 1(a). It is a plot of the detected peak intensities from the WN_x layers grown on the three substrates MgO(001), MgO(111), and Al_2O_3 (0001), as a function of deposition temperature $T_s = 500$ -800 °C. At $T_s = 500$ °C, the dominant peak for all three substrates is due to the β -WN 111 reflection. In particular, the 111 peak intensity from $\text{WN}_x/\text{MgO}(111)$ is 30 cps, which is 8.6 times stronger than the 220 peak, while for $\text{WN}_x/\text{MgO}(001)$, the 111 peak (15 cps) is 5.2 times stronger than the 220 peak, and the corresponding factor for $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$ is 7.6. These factors are considerably larger than the expected ratio of 111 vs. 220 peak intensities for randomly oriented grains, with reported values of 2.8 for cubic WN [JCPDF 01-075-1012], 3.3 for cubic β - W_2N [JCPDF 00-025-1257], and ranges from 1.6-3.3 for other cubic transition metal nitrides [JCPDF 01-074-8390, 00-025-1410, 01-074-1218, 00-049-1283, 00-038-1420, 00-035-0768, 00-031-1493, 01-075-1012, 00-025-1257]. Thus, all WN_x layers grown at $T_s = 500$ °C show a clear 111 preferred orientation, consistent with reports from other cubic transition metal nitrides which exhibit 111 textures when deposited under kinetically limited conditions, that is, at low temperature and low ion-bombardment flux and/or energy, while 001 texture becomes preferred at higher temperatures and/or ion bombardment [57,58].

The WN_x layers grown at an increased temperature of $T_s = 600$ °C also exhibit a 111 texture. Their β -WN 111 XRD peak intensity is 1.2, 1.7, and 1.9 times higher than for $T_s =$

500 °C for $\text{WN}_x/\text{MgO}(001)$, $\text{WN}_x/\text{MgO}(111)$, and $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$, respectively, as indicated by the lines that connect the plotted data points in Fig. 1(a) and are drawn to guide the eye. Similarly, the 220 intensities also increase with increasing T_s , indicating that the peak ratios remain approximately constant. This suggests that the crystalline quality and/or the grain orientation along the growth direction increase with T_s , while the relative fraction of 111 vs 220 oriented grains remains approximately constant as T_s is increased from 500 and 600 °C. We note, though, that the 111 intensity for $\text{WN}_x/\text{MgO}(001)$ deposited at $T_s = 600$ °C is only 3.8 times stronger than for the β -WN 220 peak, just slightly larger than the expected factor of 2.8 for randomly orientated β -WN, indicating a relatively weak 111 preferred orientation for this $\text{WN}_x/\text{MgO}(001)$ layer in comparison to the 2.4-2.9-times stronger textured $\text{WN}_x/\text{MgO}(111)$ and $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$ layers determined from comparison of the 111 and 220 peak intensities. We attribute the weak 111 texture on $\text{MgO}(001)$ to an epitaxial bias that favors 001 oriented WN_x , while kinetic constraints still favor a 111 orientation.

Increasing T_s to 700 °C results in considerable microstructural changes: Growth on $\text{MgO}(111)$ yields an XRD **pattern** with a single intense β -WN 111 peak of 1250 cps at 37.36°, while no other WN_x grain orientation or phase can be detected. The 111 peak is 25 times more intense than the corresponding peak for $T_s = 600$ °C, indicating strong 111-alignment for this layer and, in combination with previously reported XRD ϕ -scans and reciprocal space maps [35], demonstrates epitaxial growth of β -WN(111) on $\text{MgO}(111)$. Similarly, WN_x deposited on $\text{MgO}(001)$ results in a dominant XRD peak. In this case it is a β -WN 002 peak of 2000 cps at 42.72°, while secondary β -WN 111 and 220 peaks are 2-3 orders of magnitude weaker with 10 and 7 cps, respectively. Consistent with our previous report in Ref. [35], this layer consists of an epitaxial β - $\text{WN}_x(001)/\text{MgO}(001)$ matrix with a small concentration of misoriented β -WN grains.

In contrast, deposition on $\text{Al}_2\text{O}_3(0001)$ at $T_s = 700^\circ\text{C}$ results in a 111-textured polycrystalline layer, as also shown in Fig. 2(a). That is, for $\text{Al}_2\text{O}_3(0001)$ substrates, the trend from $T_s = 500$ and 600°C is continued to $T_s = 700^\circ\text{C}$: The ratio between the different β -WN XRD peak intensities remains independent of T_s , while the crystalline quality and/or the grain orientation continues to improve, based on the 50-94% higher XRD peak intensities for $T_s = 700^\circ\text{C}$ vs $T_s = 600^\circ\text{C}$. In addition, the XRD **pattern** from this layer also exhibits relatively weak 110 and 211 BCC W peaks with 12 and 2 cps, indicating that a small fraction of grains in this layer have lost the majority of their nitrogen.

For the highest growth temperature $T_s = 800^\circ\text{C}$, all XRD **patterns** are dominated by peaks associated with the α -W (BCC) phase. The **pattern** from the $\text{WN}_x/\text{MgO}(001)$ layer exhibits strong α -W 002 and 110 peaks with 1420 and 440 cps, respectively, a weaker α -W 211 peak with 30 cps, and also a very weak β -WN 220 peak with 3.5 cps, indicating that only a small fraction of this layer forms a nitride phase. $\text{WN}_x/\text{MgO}(111)$ shows a single intense α -W 110 peak of 8200 cps. Similarly, the **pattern** from the $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$ layers exhibits an intense α -W 110 peak of 7150 cps, but also a weak β -W 211 peak of 6 cps, a weak α -W 211 of 5.5 cps and a β -WN 002 peak of 22 cps. These results from $T_s = 800^\circ\text{C}$ indicate nitrogen loss in WN_x layers at elevated temperatures, as discussed more quantitatively in the following paragraph.

Figure 3 is a plot of the nitrogen to tungsten ratio x , as measured by EDS using a light-element-sensitive setup as described in the experimental section. The WN_x layers grown at $T_s = 500^\circ\text{C}$ are overstoichiometric, with measured compositions of $\text{WN}_{1.20}$ deposited on $\text{MgO}(001)$, $\text{WN}_{1.17}$ deposited on $\text{MgO}(111)$, and $\text{WN}_{1.11}$ deposited on $\text{Al}_2\text{O}_3(0001)$. The corresponding compositions for $T_s = 600^\circ\text{C}$ are $x = 1.21$, 1.14, and 1.12, indicating negligible changes in the nitrogen content between 500 and 600°C . In contrast, x decreases to 0.92, 0.83, and 0.93 for $T_s =$

700 °C and drops to $x = 0.06$, 0.06 , and 0.04 , respectively. These results are confirmed by x-ray photoelectron spectroscopy (not shown), which yield compositions within $\pm 3\%$ from those obtained by EDS with, for example, $x = 0.92$, 0.81 , and 0.90 for WN_x grown at $T_s = 700$ °C on $\text{MgO}(001)$, $\text{MgO}(111)$, $\text{Al}_2\text{O}_3(0001)$, respectively.

The data in Fig. 3 clearly shows a decrease in the N-content with increasing T_s , from overstoichiometric WN_x for $T_s \leq 600$ °C, to understoichiometric WN_x for $T_s = 700$ °C, to nearly N-free WN_x for $T_s = 800$ °C. This trend is consistent with the XRD data, as **patterns** for $T_s \leq 700$ °C exhibit β -WN peaks while the dominant peaks for $T_s = 800$ °C are associated with the α -W phase. We propose that the residual 4-6% N in samples deposited at 800 °C is due to small amounts of nitrogen remaining in α -W grains for $\text{WN}_x/\text{MgO}(111)$ or due to small β -WN grains for $\text{WN}_x/\text{MgO}(001)$ or $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$, as described in the above XRD results. **We note that the XRD analysis in Fig. 2 indicates that the $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$ layer with $T_s = 700$ °C also contains α -W. This, in turn, means that the WN_x grains in this layer may have a larger N-content than the overall measured composition of $x = 0.93$. However, the detected α -W 110 XRD peak is approximately three orders of magnitudes weaker than the corresponding peak for the $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$ layer grown at $T_s = 800$ °C, suggesting that the α -W fraction in the $T_s = 700$ °C layer is very small, rendering this effect negligible. Therefore, for point defect concentration analyses below, we assume $x = 0.93$ is applicable for the WN_x grains in the $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$ layer with $T_s = 700$ °C.** A decrease in the N-to-metal ratio with increasing T_s has been reported for various other transition metal nitrides including NbN_x above 900 °C [17], CrN_x above 730 °C [59], HfN_x above 650 °C [13], and TaN_x above 400 °C [60], and has been attributed to a higher rate of nitrogen recombination and desorption at higher temperature, and the increasing importance of the entropy contribution to the free energy of the N_2 gas [17,61].

The measured N-content varies for different substrates, as presented in Fig. 3, this difference is relatively small (3-12%), but larger than the measurement uncertainty of $\pm 3\%$. The reason for the differences is not known, but may be attributed to slight differences in the actual substrate temperature during deposition at nominally identical T_s , or also related to the changes in the nitrogen incorporation kinetics which is expected to be a function of the crystalline facet and therefore of the preferred layer orientation which is affected by the substrate.

Figure 4(a) is a plot of the lattice constant for the cubic β -WN phase vs N-to-W ratio x . It is determined from the XRD peak positions of the strongest reflections in the θ - 2θ patterns from each of the WN_x layers grown on $\text{MgO}(001)$, $\text{MgO}(111)$, and $\text{Al}_2\text{O}_3(0001)$ at $T_s = 500, 600$, and 700°C . The plot does not include data from the $T_s = 800^\circ\text{C}$ samples, since they consist primarily of the BCC-W phase and possibly small inclusions of β -WN that cannot be detected or, for the case of $\text{WN}_x/\text{MgO}(001)$, can be detected but have unknown composition since the N-content is not expected to match the measured average composition ($x = 0.06$) of the entire film which consists mostly of BCC-W. For all substrates, the lattice constant increases with increasing x , indicating that the lattice expands to incorporate the additional nitrogen, as also indicated by the dashed purple line which is a linear fit through all data points. More specifically, it increases for the $\text{WN}_x/\text{MgO}(001)$ layers from $4.234 \pm 0.009 \text{ \AA}$ for $x = 0.92$ grown at $T_s = 700^\circ\text{C}$ to $4.322 \pm 0.012 \text{ \AA}$ and $4.339 \pm 0.023 \text{ \AA}$ for $x = 1.21$ and 1.20 with $T_s = 600^\circ\text{C}$ and 500°C . For $\text{WN}_x/\text{MgO}(111)$, the lattice constant also increases with increasing x from $4.169 \pm 0.001 \text{ \AA}$ for $x = 0.83$ deposited at $T_s = 700^\circ\text{C}$ to $4.301 \pm 0.115 \text{ \AA}$ for $x = 1.14$ at 600°C and $4.357 \pm 0.118 \text{ \AA}$ for $x = 1.17$ at $T_s = 500^\circ\text{C}$. The two samples deposited on $\text{MgO}(111)$ at the lower temperatures of $T_s = 500$ - 600°C show larger error bars in the lattice constant due to the proximity of the 111 peak from the WN_x layers to the intense MgO 111 substrate peaks. The lattice constant of

$\text{WN}_x/\text{Al}_2\text{O}_3(0001)$ increases from $4.173 \pm 0.070 \text{ \AA}$ for $x = 0.93$ deposited at $T_s = 700 \text{ }^\circ\text{C}$ to $4.314 \pm 0.015 \text{ \AA}$ for $x = 1.12$ at $600 \text{ }^\circ\text{C}$ and $4.325 \pm 0.023 \text{ \AA}$ for $x = 1.11$ deposited at $T_s = 500 \text{ }^\circ\text{C}$. The large error bar in the lattice constant for the $\text{WN}_{0.93}/\text{Al}_2\text{O}_3(0001)$ sample deposited at $700 \text{ }^\circ\text{C}$ suggests strain or composition variations throughout the sample, causing a varying lattice constant [62], consistent with the observation presented in Figs. 2(a) and (b) that this sample contains small inclusions of BCC W grains which may be the result of spatial or temporal temperature variations, estimated to be $\pm 25 \text{ }^\circ\text{C}$, during growth of this sample. We also note that the plotted values are out-of-plane lattice constants which may, due to strain, slightly differ from the relaxed lattice constants. For example, a biaxial compressive stress would lead to an out-of-plane lattice constant that is greater than the corresponding relaxed lattice constant [11]. We have previously reported on our efforts to measure the strain in epitaxial WN_x layers by XRD reciprocal space mapping, and have found in-plane strain values which are comparable to the experimental uncertainty, with values of $\varepsilon_{||} = 0.023 \pm 0.020$ (tensile) and $\varepsilon_{||} = -0.001 \pm 0.002$ (relaxed) for $\text{WN}/\text{MgO}(111)$ and $\text{WN}/\text{MgO}(001)$ grown at $T_s = 700 \text{ }^\circ\text{C}$, respectively [35].

We discuss the measured lattice constants for cubic WN_x using the calculated values presented in section 3 for stoichiometric and off-stoichiometric compositions. For this purpose, the fitting curves presented in Fig. 1(b) are reproduced in Fig. 4(a), illustrating the predicted lattice constants for $\beta\text{-WN}_x$ where the upper left and right curves correspond to a rock-salt structure containing N or W vacancies, respectively, and the lower left and right curves correspond to WN_x in the NbO structure with some of the cation or anion vacant positions filled with W or N, respectively. The experimental data can be divided into two regions: (1) Layers deposited at $T_s = 500\text{--}600 \text{ }^\circ\text{C}$ have lattice constants of $4.30 - 4.36 \text{ \AA}$ and compositions of $x = 1.11 - 1.21$. These data points are near the upper right simulation curve, suggesting that their

structure can be described as a rock-salt phase that contains tungsten vacancies. (2) In contrast, growth at $T_s = 700$ °C yields $a = 4.17 - 4.23$ Å and $x = 0.83 - 0.93$. This group of data points approximately match the lower left curve, indicating that the structures may be best described by a NbO phase for which some vacant cation sites are filled with W. To illustrate this point further, Fig. 4(b) is a plot of the tungsten and nitrogen vacancy concentrations V_W and V_N for the nine measured lattice constants presented in Fig. 4(a). The plotted values are determined using Eq. (1) including the numerical values for α , β , and γ that correspond to the lines in Figs. 1(b) and 4(a), and using the expression $x = (1-V_N)/(1-V_W)$ which relates the overall composition to the vacancy concentrations.

The tungsten vacancy concentration is 11-18% for the layers which are grown at 700 °C and are understoichiometric with $x = 0.83-0.93$. It decreases to $V_W = 6-11\%$ for the overstoichiometric layers with $x = 1.11-1.21$ and $T_s = 500-600$ °C. This decreasing trend with increasing x is also indicated in Fig. 4(b) with a dashed line obtained from a linear fit. The trend is initially counter intuitive, since a decreasing V_W corresponds to an increasing occupation of cation sites, while an increasing x corresponds to an increasing anion to cation ratio. We attribute the negative slope of V_W vs x primarily to a temperature effect, while the change in x is accounted for by nitrogen vacancies as discussed below. More specifically, an increase in growth temperature leads to a larger tungsten vacancy concentration. This is fully consistent with our first-principles calculations showing that the NbO structure is more stable than the rock-salt structure. Thus, our predicted lowest energy configurations exhibit $V_W = 25\%$. Correspondingly, increasing T_s is expected to lead to structures which are closer to thermodynamic equilibrium, which corresponds to an increase in V_W towards the predicted maximum of 25%, exactly as observed experimentally. The nitrogen vacancy concentration shows a much stronger

composition dependence, decreasing from $V_N = 18\text{-}29\%$ for $x = 0.83\text{-}0.93$ to a negative $V_N = -2\%$ to -10% for $x = 1.11\text{-}1.21$. The negative values are a direct consequence of data points in Fig. 4(a) laying above the curve for the rock-salt structure containing W vacancies, which may be attributed to compressive strains, nitrogen interstitials, occupation of cation sites by N, or the formation of N-bubbles within the layer which form due to implantation of backscattered neutrals, as has previously been reported for other transition metal nitrides [63], and would correspond to a smaller-than-measured N-concentration within the WN_x matrix. However, independent of the exact origin for the (unphysical) slightly negative V_N values, the overall trend of a steeply decreasing V_N with increasing x is evident, as also indicated by the dashed line through the data. This trend shows that the decreasing anion-to-cation ratio with increasing T_s is primarily accounted for by nitrogen vacancies. In summary, both W and N vacancy concentrations decrease with increasing x in WN_x layers. This trend is primarily attributed to growth temperature effects, where a larger T_s helps to overcome kinetic barriers to move the system closer to the equilibrium structure, that is (1) towards the thermodynamically favorable cubic NbO structure which corresponds to the rock-salt structure with 25% of both W and N vacancies, and (2) to a lower N content within the nitride due to the high entropy of the competing N_2 vapor phase.

Figure 5 shows measured physical properties including electrical resistivity ρ , elastic modulus E and hardness H of $\text{WN}_x/\text{MgO}(001)$, $\text{WN}_x/\text{MgO}(111)$, and $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$ layers as a function of $T_s = 500\text{-}800$ °C. The measured resistivity plotted in Fig. 5(a) decreases continuously with increasing growth temperature for all three sample sets. For $T_s = 500$ °C, $\rho = 4.5 \pm 0.2 \times 10^3$, $4.4 \pm 0.2 \times 10^3$, and $4.5 \pm 0.2 \times 10^3$ $\mu\Omega\text{-cm}$ for layers grown on $\text{MgO}(001)$, $\text{MgO}(111)$, and $\text{Al}_2\text{O}_3(0001)$, respectively. The values decrease to $2.7 \pm 0.1 \times 10^3$, $2.6 \pm 0.1 \times 10^3$,

and $3.2 \pm 0.1 \times 10^3 \mu\Omega\text{-cm}$ for $T_s = 600^\circ\text{C}$ and to $1.6 \pm 0.1 \times 10^3$, $1.9 \pm 0.1 \times 10^3$, and $1.1 \pm 0.2 \times 10^3 \mu\Omega\text{-cm}$ for $T_s = 700^\circ\text{C}$. That is, the WN_x layers in this study exhibit a range of resistivities from $1.1\text{--}4.5 \times 10^{-5} \Omega\text{-m}$, which is within the range of previously reported values for WN_x of $0.1\text{--}5.0 \times 10^{-5} \Omega\text{-m}$ [26,37,41,64–66], while other reports on WN_x layers including samples obtained by MOCVD or sputtering at high working gas pressures or high ion bombardment energies indicate even higher resistivities ranging from $10^{-4} - 10^{-1} \Omega\text{-m}$ [33,38,39,44,67,68], which is likely due to their lower crystalline quality. The layers grown at $T_s = 800^\circ\text{C}$, which, as discussed above, consist primarily of BCC-W grains and have a low nitrogen concentration corresponding to $x = 0.06$, 0.06 , and 0.04 , respectively, have resistivities of 50 ± 2 , 42 ± 1 , and $48 \pm 2 \mu\Omega\text{-cm}$. These values are higher than the reported $5.3 \mu\Omega\text{-cm}$ for pure bulk W [69], likely due to the nonzero nitrogen content in these films. However, W films that were sputter deposited in Ne gas at room temperature have been reported to exhibit a considerably higher resistivity of $132 \mu\Omega\text{-cm}$ [67].

We attribute the decrease in resistivity with increasing T_s primarily to an increased crystalline quality and grain size at higher deposition temperatures, reducing the weak carrier localization which has been used to describe electron transport in various transition metal nitrides including $\text{CrN}(001)$ [70,71], $\text{HfN}_x(001)$ [13], $\text{TaN}_x(001)$ [18], $\text{Sc}_{1-x}\text{Ti}_x\text{N}(001)$ [72], $\text{Ti}_{1-x}\text{W}_x\text{N}(001)$ [73], $\text{Sc}_{1-x}\text{Al}_x\text{N}(001)$ [74], NbN [17], and $\text{NbC}_x\text{N}_{1-x}(001)$ [61]. In addition, the larger N vacancy concentration at higher T_s may also contribute to the reduced resistivity, as nitrogen vacancies introduce additional electron carriers, raising the Fermi level further into the W $5d$ bands, which leads to more metallic conduction and may more than compensate for the expected additional electron scattering [11] at the localized states of N vacancies. In addition, we note the minor differences in resistivities measured for samples grown at the same temperature

but on different substrates, which we attribute to microstructural differences including grain size, orientation, and grain boundary structure. In particular, the substrate affects the nucleation kinetics and therefore the nuclei size which, in turn, determines the column width, but also the preferred orientation which affects grain boundaries and the length scales for surface diffusion, resulting in variations in grain size and grain boundary electron reflection coefficients.

The elastic modulus of the WN_x layers is plotted in Fig. 5(b), showing the trends in the elastic moduli versus growth temperature for the three different substrates. $WN_x/MgO(111)$ layers exhibit an elastic modulus which is nearly independent of $T_s = 500-700$ °C, varying only from 253 ± 30 to 288 ± 40 to 259 ± 9 GPa despite the variation in microstructure and nitrogen content. Layers on $Al_2O_3(0001)$ show similar overall moduli as on $MgO(111)$, but suggest a slight increase from $E = 201 \pm 21$ to 208 ± 22 to 242 ± 17 GPa for $T_s = 500, 600,$ and 700 °C, respectively. In contrast, the $WN_x/MgO(001)$ layers have considerably lower moduli and show a clear increase with increasing growth temperature, from 110 ± 5 GPa to 137 ± 16 GPa to 238 ± 61 GPa for $T_s = 500, 600,$ and 700 °C, respectively. The elastic moduli for the nitrogen rich samples deposited at $T_s = 500 - 600$ °C exhibit a distinct dependence on the substrate. In particular, E is largest for $WN_x/MgO(111)$, smaller for $WN_x/Al_2O_3(0001)$, and smallest for $WN_x/MgO(001)$. This is exactly the same trend as observed in Fig. 2(b) for the 111-texture, with the strongest 111 preferred orientation for $WN_x/MgO(111)$, a weaker texture for $WN_x/Al_2O_3(0001)$ and only a slight 111 preferred orientation for $WN_x/MgO(001)$. Therefore, we attribute the particularly low elastic moduli for $WN_x/MgO(001)$ deposited at 500 and 600°C to the weak 111 texture. In addition, these two samples have the highest measured N content with $x = 1.20$ and 1.21 , which may cause a low adatom mobility during deposition [75] due to a high N surface coverage, and therefore may result in underdense grain boundaries and an overall underdense microstructure

which is expected to be the cause for the reduced elastic modulus. In contrast, $T_s = 700$ °C yields E values that are nearly independent of the substrate, suggesting that the higher crystalline quality of these layers in combination with the lower N content define the modulus more consistently. This is so despite that the different substrates result in different crystalline orientations of the WN_x , suggesting that the elastic anisotropy of β -WN is small/negligible, which is, however, in contradiction with our previous work suggesting an elastic anisotropy ratio of $A = 1.6$ [35]. The layers deposited at $T_s = 800$ °C have measured elastic moduli of 236 ± 29 , 274 ± 10 , and 354 ± 14 GPa. These layers contain only 4-6% N, they consist primarily of the BCC W phase, and their elastic modulus is in between 410 and 209 GPa, the known bulk value for pure W and the reported modulus for a $0.25 \mu\text{m}$ thick W layer on Si [76].

The measured elastic moduli from our β -WN layers can be compared to previous studies in which nanoindentation has been used to determine mechanical properties of WN_x layers [28,32–34,38,40,43]. Reported values for the WN_x elastic modulus range from $E = 240$ -430 GPa [32,34,40], with an increase in the N-to-W ratio from $x = 0.61$ -0.71 leading to a decrease in E from 305-275 GPa [40], or for $x = 0.43$, 0.89, and 1.38 to $E = 380$, 380, and 325 GPa [32], with the latter value being further reduced through strain relaxation upon annealing to $E = 285$ GPa [32]. This suggests that an increase in nitrogen content results in a decrease in the elastic modulus, consistent with the relatively low E values of our samples with large N contents of $x \geq 1.20$. We note here that smaller N-to-W ratios also yield a reduced modulus $E_r = 279$ -224 GPa for samples with $x = 0.17$ -0.5 deposited by PLD and $E_r = 313$ -284 GPa for sputtered WN_x with $x = 0.11$ -0.25 [34], while phase and intrinsic stress also affect E , for example, hexagonal $WN_{1.17}$ with a compressive stress of -12.6 GPa exhibits a high $E = 430$ GPa [40].

The hardness of the WN_x samples is presented in Fig. 5(c) as a function of T_s for the three substrate types. It is relatively independent on both the growth temperature and the substrate. The hardness of $\text{WN}_x/\text{MgO}(001)$ varies from $H = 9.7 \pm 0.8$ to 12.6 ± 2.5 , 9.8 ± 3.9 , and 7.1 ± 1.1 GPa at $T_s = 500$ °C, 600 °C, 700 °C, and 800 °C respectively. $\text{WN}_x/\text{MgO}(111)$ increases in hardness from $H = 11.7 \pm 2.0$ GPa at 500 °C to 12.9 ± 2.6 GPa at 600 °C before decreasing to 12.4 ± 1.0 GPa at 700 °C and further to 7.2 ± 0.5 at 800 °C. $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$ layers show a similar behavior, with H varying from 10.4 ± 1.6 to 12.7 ± 2.2 , 10.2 ± 0.8 , and 7.3 ± 0.4 GPa. The hardness values for the nearly N-free samples deposited at $T_s = 800$ °C, 7.1 ± 1.1 , 7.2 ± 0.5 , and 7.3 ± 0.4 GPa, are between the reported bulk value for W of 6.6 ± 0.2 GPa and the reported 8 GPa for 1- μm -thick W deposited on MgO [76].

The hardness of WN_x has previously been reported to range from 5-39 GPa [28,33,34,38,40,43]. This large range is attributed to variations in microstructure, nitrogen content, layer density, and phase content. For example, the reported H decreases from 32 to 26 GPa as x increases in cubic WN_x from 0.35 to 0.7, but H increases again with increasing $x > 0.75$ due to the formation of hexagonal phase inclusions [40]. In addition, H is reported to increase with deposition power and nitrogen partial pressure but decrease with total gas pressure, providing a large range from 6-30 GPa in a single study [33]. Our hardness values fall within the lower half of the previously reported range, which we attribute to the β -WN phase despite the high $x = 0.83$ -1.21 and a relatively low ion-implantation defect density associated with the absence of an intentional substrate bias as well as with the relatively high deposition temperatures. We also note that the measured ratio H/E is relatively low, ranging from 0.04 to 0.09. This suggests that our WN_x layers are relatively brittle, which may be attributed to the presence of both cation and anion vacancies, causing an increased bonding directionality as the

structure transitions from the rocksalt to the NbO phase, resulting in an increased shear modulus and, in turn, a more brittle mechanical response.

5. Conclusions

Polycrystalline and epitaxial WN_x layers were deposited on $\text{MgO}(001)$, $\text{MgO}(111)$, and $\text{Al}_2\text{O}_3(0001)$ substrates as a function of temperature $T_s = 500\text{-}800\text{ }^\circ\text{C}$. At low $T_s = 500\text{-}600\text{ }^\circ\text{C}$, the deposited WN_x layers are polycrystalline, exhibit a slight 111 preferred orientation, and show an increasing crystalline quality with increasing temperature. $T_s = 700\text{ }^\circ\text{C}$ results in the highest quality crystals, which are epitaxial $\beta\text{-WN}$ 111 on $\text{MgO}(111)$, epitaxial $\beta\text{-WN}$ 001 on $\text{MgO}(001)$ with small inclusions of misoriented grains, and highly 111-textured $\beta\text{-WN}$ on $\text{Al}_2\text{O}_3(0001)$ with a small inclusions of misoriented WN grains and of BCC W. Out-of-plane lattice constants decrease from 4.357-4.169 Å as T_s increases from 500-700 °C, while x decreases from 1.21 to 0.83 over the same temperature range. The resistivity decreases from 4.5×10^3 to $42\text{ }\mu\Omega\text{-cm}$ with increasing T_s , which is primarily attributed to an increasing crystalline quality and grain size which reduces the carrier localization. The measured WN_x hardness is nearly independent of the substrate. It increases slightly from 500-600 °C as the crystal quality increases, decreases slightly from 600-700 °C as the nitrogen content decreases, and decreases some more to 7.1 GPa for layers deposited at 800 °C which consist of mostly BCC W. Elastic moduli measured by nanoindentation show a wide variation between the three substrates at 500-600 °C due to the different degree of 111 preferred orientation which causes changes in the nitrogen surface coverage, adatom mobility and, in turn, layer density. $T_s = 700\text{ }^\circ\text{C}$ results in more consistent values with $E = 238\text{-}259\text{ GPa}$, which may be attributed to the higher crystalline quality and/or lower N content of these layers. Density functional calculations indicate that cubic WN_x is

considerably more stable in the NbO than the rock-salt structure. The predicted lattice constants as a function of x for both, the vacancy-containing rock-salt structure and the NbO structure where some of the vacant sites filled, are used to interpret the experimentally measured lattice constants and to quantitatively determine the W and N vacancy concentrations. V_W increases slightly and V_N increases strongly with increasing T_s and a simultaneously decreasing x . The latter is attributed to N-loss at elevated temperatures associated with the large entropy of N_2 gas, while the increase in the density of both vacancy types suggests that the increased atomic mobility during deposition leads to a structure approaching the thermodynamically favored NbO structure.

Acknowledgements

The authors acknowledge support by the National Science Foundation under Grant Nos. 1309490, 1234777, 1234872, 1537984, and 1629230. Computational resources were provided by the Center for Computational Innovations at RPI.

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Figure Captions:

Figure 1: (a) Formation energy **per atom** E_f and (b) lattice constant a , of cubic WN_x as a function of N-to-W ratio x obtained from first-principles simulations **using a cubic supercell with 32 cation and 32 anion sites**. The left top quadrant (red circles, $x < 1$) is for structures with 32 W and 24-32 N atoms, corresponding to rock-salt WN_x containing N vacancies. Similarly: *right top*: (red circles, $x > 1$), 24-32 W and 32 N atoms; *left bottom*: (blue squares, $x < 1$); 24-32 W and 24 N atoms, *right bottom*: (blue squares, $x > 1$), 24 W and 24-32 N atoms. The triangle is for an ordered structure (28 W and 28 N atoms) half-way between rock-salt and NbO. Dashed lines are obtained from data fitting using Eq. (1).

Figure 2: (a) X-ray diffraction (XRD) **patterns** for $WN_x/Al_2O_3(0001)$ layers deposited at $T_s = 500, 600, 700, \text{ and } 800^\circ\text{C}$, and (b) summary plot from WN_x deposited on $MgO(001)$, $MgO(111)$, and $Al_2O_3(0001)$, showing measured XRD peak intensities from β -WN 111, 220, 002, and 311, from α -W 110, 002, and 211, and from β -W 211 reflections, vs $T_s = 500\text{-}800^\circ\text{C}$.

Figure 3: Measured N/W ratio x vs deposition temperature T_s of WN_x layers.

Figure 4: (a) Measured out-of-plane lattice constants a vs composition x of WN_x layers deposited on $MgO(001)$, $MgO(111)$, and $Al_2O_3(0001)$. The dashed purple line is a linear fit through all data points while the black symbols for stoichiometric WN in the rock-salt and NbO structures and the black dashed lines are computational results reproduced from Fig. 1(b). (b) Tungsten and nitrogen vacancy concentrations V_W and V_N , as obtained from the measured lattice constants and

Eq. (1). Circles, squares, and triangles represent data from $\text{WN}_x/\text{MgO}(001)$, $\text{WN}_x/\text{MgO}(111)$, and $\text{WN}_x/\text{Al}_2\text{O}_3(0001)$, respectively, while lines are from linear fitting.

Figure 5: (a) Resistivity ρ , (b) Young's modulus E , and (c) hardness H , vs deposition temperature T_s of WN_x samples deposited on $\text{MgO}(001)$, $\text{MgO}(111)$, and $\text{Al}_2\text{O}_3(0001)$.

Figure 1

Figure 2

Figure 3

Figure 4

Figure 5